

**MD.23.**

**Title** High resolution semiconductor switch

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**Patent no.** Pending patent registration

**Description****EN**

The active layer of the high resolution semiconductor switch is based on single crystal compound  $\text{Ag}_3\text{AsS}_3$  placed between metal electrodes. The switching time from high to low ohmic state of the device consists tenths of seconds and depends on the applied voltage. The change of switching time to low ohmic state occurs if applying mechanical pressure on the active layer. This structure can be used to manufacture high precision electronic scales, as it permits to measure weights of  $5 \cdot 10^{-5}$  grams. The structure is also sensible to vibrations.

**Class no.** 5,10